



ON Semiconductor®

# J109 / MMBFJ108 N-Channel Switch

## Features

- This device is designed for digital switching applications where very low on resistance is mandatory.
- Sourced from process 58

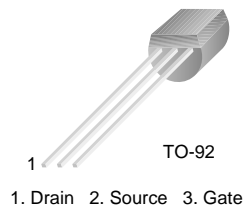


Figure 1. J109 Device Package

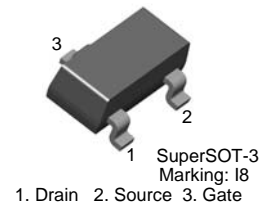


Figure 2. MMBFJ108 Device Package

## Ordering Information

Part Number	Top Mark	Package	Packing Method
J109	J109	TO-92 3L	Bulk
J109-D26Z	J109	TO-92 3L	Tape and Reel
MMBFJ108	I8	SSOT 3L	Tape and Reel

## Absolute Maximum Ratings<sup>(1), (2)</sup>

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$V_{DG}$	Drain-Gate Voltage	25	V
$V_{GS}$	Gate-Source Voltage	-25	V
$I_{GF}$	Forward Gate Current	10	mA
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Notes:

1. These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .
2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

### Thermal Characteristics

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Max.		Unit
		J109 <sup>(3)</sup>	MMBFJ108 <sup>(4)</sup>	
$P_D$	Total Device Dissipation	625	350	mW
	Derate Above $25^\circ\text{C}$	5.0	2.8	mW/ $^\circ\text{C}$
$R_{\theta\text{JC}}$	Thermal Resistance, Junction-to-Case	125		$^\circ\text{C/W}$
$R_{\theta\text{JA}}$	Thermal Resistance, Junction-to-Ambient	200	357	$^\circ\text{C/W}$

**Notes:**

- PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.
- Device mounted on FR-4 PCB 36mm x 18mm x 1.5mm; mounting pad for the collector lead minimum 6cm<sup>2</sup>.

### Electrical Characteristics

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit	
<b>Off Characteristics</b>						
$V_{(\text{BR})\text{GSS}}$	Gate-Source Breakdown Voltage	$I_G = -10 \mu\text{A}, V_{\text{DS}} = 0$	-25		V	
$I_{\text{GSS}}$	Gate Reverse Current	$V_{\text{GS}} = -15 \text{ V}, V_{\text{DS}} = 0$		-3.0	nA	
		$V_{\text{GS}} = -15 \text{ V}, V_{\text{DS}} = 0, T_A = 100^\circ\text{C}$		-200		
$V_{\text{GS(off)}}$	Gate-Source Cut-Off Voltage	$V_{\text{DS}} = 15 \text{ V}, I_D = 10 \text{ nA}$	MMBFJ108	-3.0	-10.0	V
			J109	-2.0	-6.0	
<b>On Characteristics</b>						
$I_{\text{DSS}}$	Zero-Gate Voltage Drain Current <sup>(5)</sup>	$V_{\text{DS}} = 15 \text{ V}, V_{\text{GS}} = 0$	MMBFJ108	80		mA
			J109	40		
$r_{\text{DS(on)}}$	Drain-Source On Resistance	$V_{\text{DS}} \leq 0.1 \text{ V}, V_{\text{GS}} = 0$	MMBFJ108		8.0	$\Omega$
			J109		12	
<b>Small Signal Characteristics</b>						
$C_{\text{dg(on)}}$ $C_{\text{sg(off)}}$	Drain-Gate & Source-Gate On Capacitance	$V_{\text{DS}} = 0, V_{\text{GS}} = 0, f = 1.0 \text{ MHz}$		85	pF	
$C_{\text{dg(off)}}$	Drain-Gate Off Capacitance	$V_{\text{DS}} = 0, V_{\text{GS}} = -10 \text{ V}, f = 1.0 \text{ MHz}$		15	pF	
$C_{\text{sg(off)}}$	Source-Gate Off Capacitance	$V_{\text{DS}} = 0, V_{\text{GS}} = -10 \text{ V}, f = 1.0 \text{ MHz}$		15	pF	

**Note:**

- Pulse test: pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

Typical Performance Characteristics

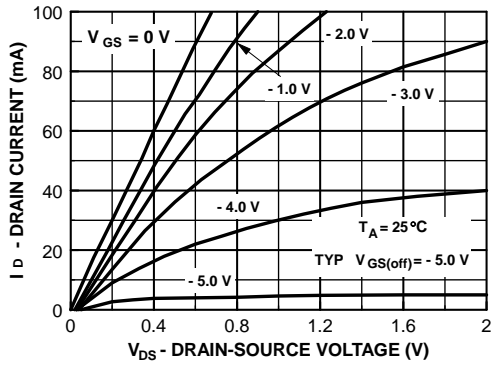


Figure 3. Common Drain-Source

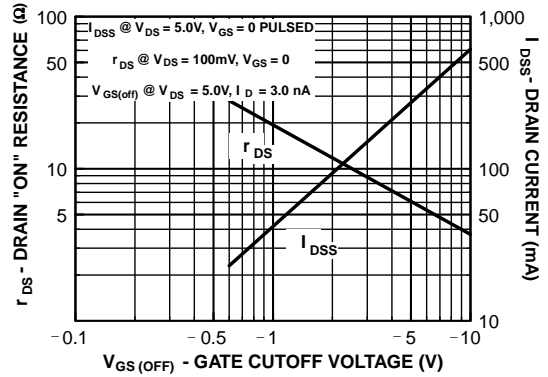


Figure 4. Parameter Interactions

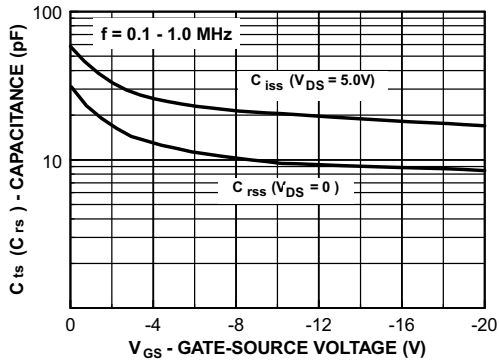


Figure 5. Common Drain-Source

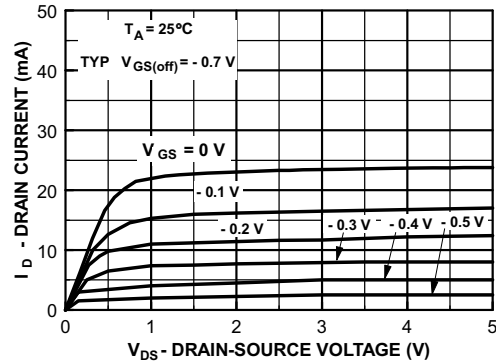


Figure 6. Common Drain-Source

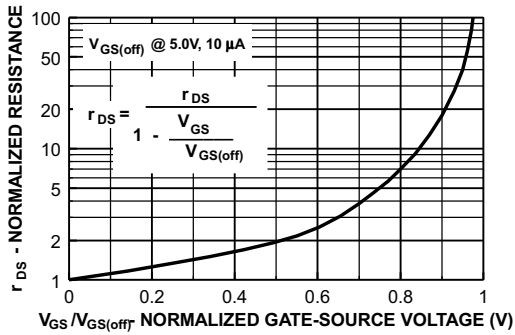


Figure 7. Normalized Drain Resistance vs. Bias Voltage

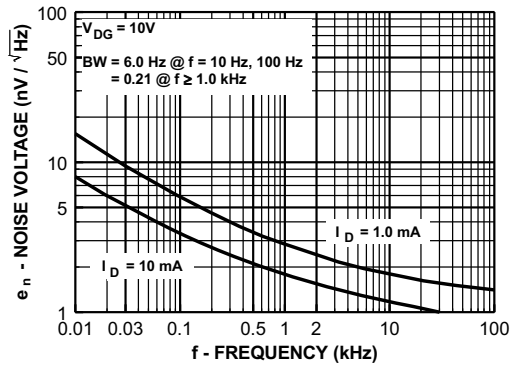


Figure 8. Noise Voltage vs. Frequency

Typical Performance Characteristics (Continued)

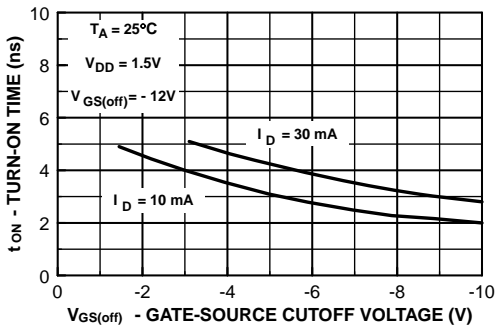


Figure 9. Switching Turn-On Time vs. Gate-Source Cut-Off Voltage

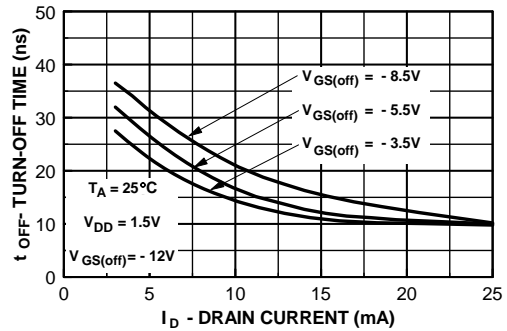


Figure 10. Switching Turn-Off Time vs. Drain Current

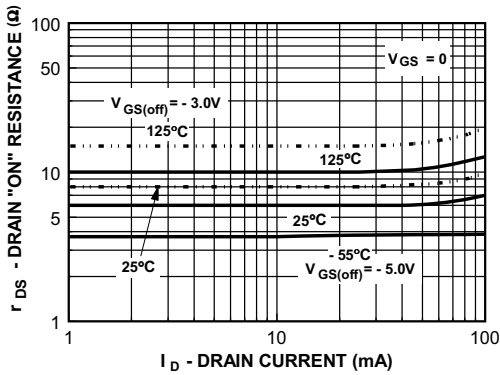


Figure 11. On Resistance vs. Drain Current

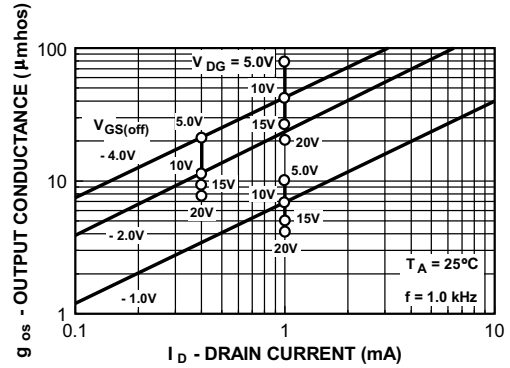


Figure 12. Output Conductance vs. Drain Current

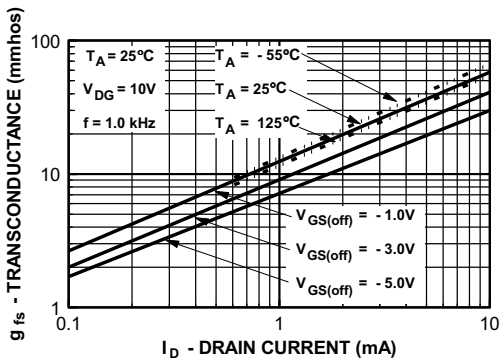


Figure 13. Transconductance vs. Drain Current

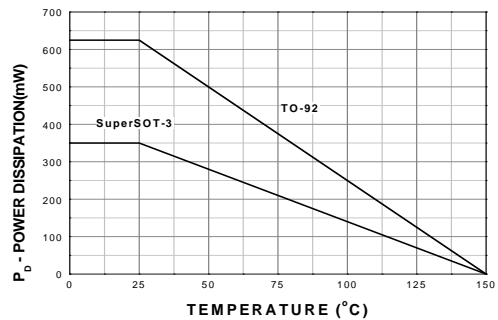
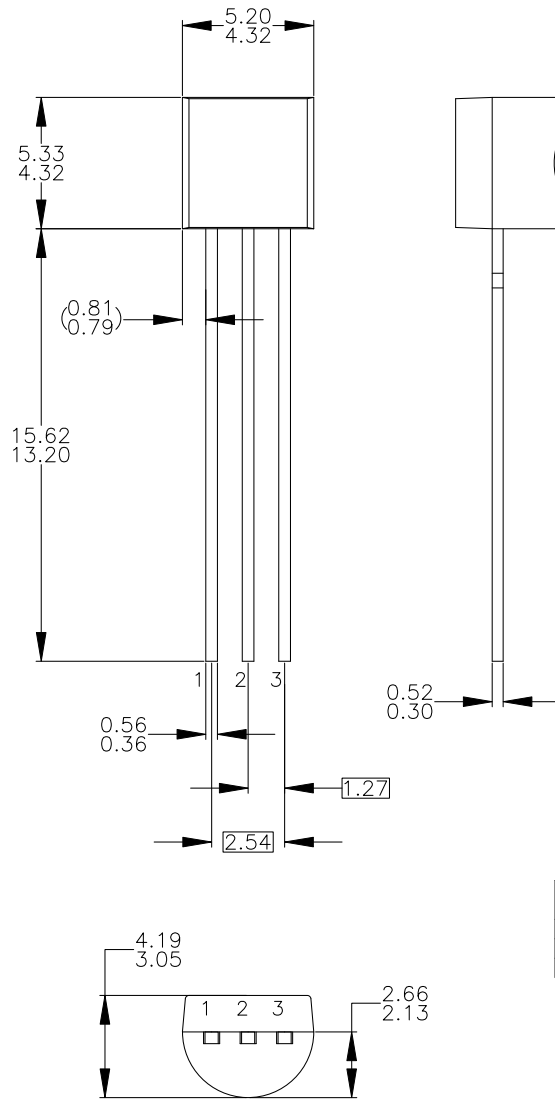


Figure 14. Power Dissipation vs. Ambient Temperature

Physical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994.
- D) TO-92 (92,94,96,97,98) PIN CONFIGURATION:

PIN	92			94			96			97			98		
	P	F	M	P	F	M	B	F	M	P	F	M	P	F	M
1	E	S	S	E	S	S	B	D	G	C	G	D	C	G	D
2	B	D	G	C	G	D	E	S	S	B	D	G	E	S	S
3	C	G	D	B	D	G	C	G	D	E	S	S	B	D	G

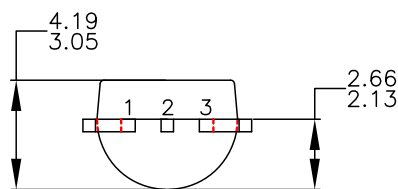
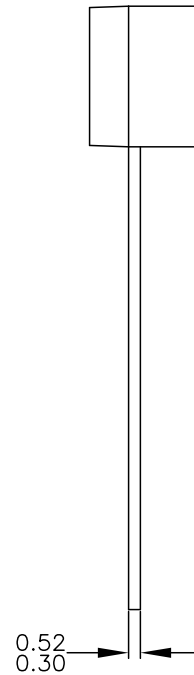
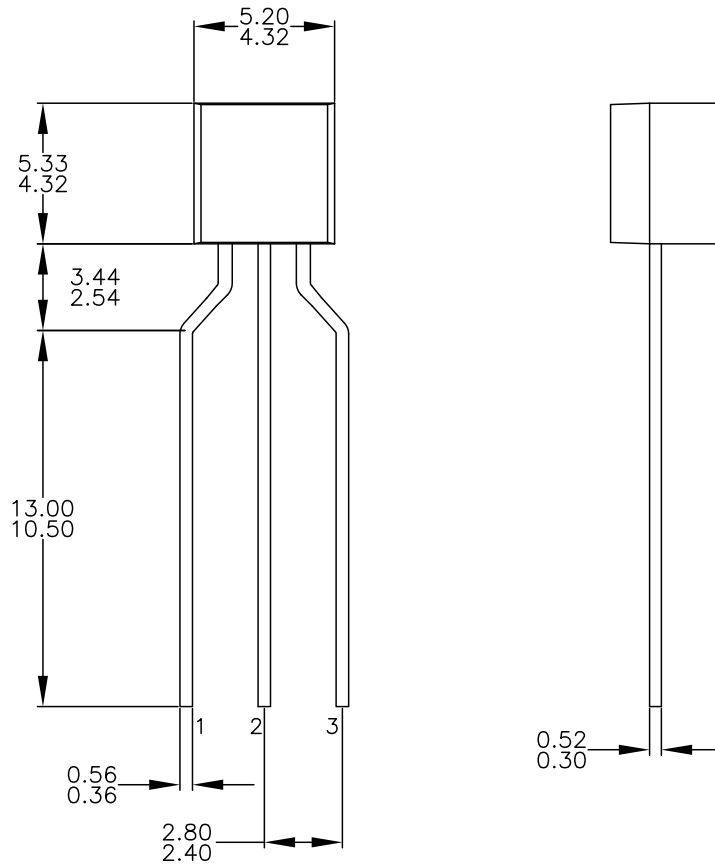
LEGEND:

- P - BIPOLAR
- F - JFET
- M - DMOS
- E - EMITTER
- B - BASE
- C - COLLECTOR
- D - DRAIN
- S - SOURCE
- G - GATE

- E) FOR PACKAGE 92, 94, 96, 97 AND 98: PIN CONFIGURATION DRAIN "D" AND SOURCE "S" ARE INTERCHANGEABLE AT JFET "F" OPTION.
- F) DRAWING FILENAME: MKT-ZA03DREV3.

Figure 15. 3-Lead, TO-92, JEDEC TO-92 Compliant Straight Lead Configuration, Bulk Type

Physical Dimensions (Continued)

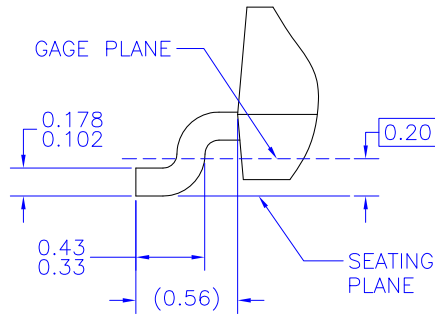
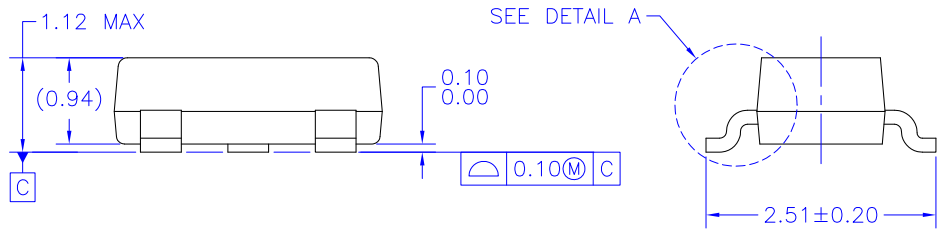
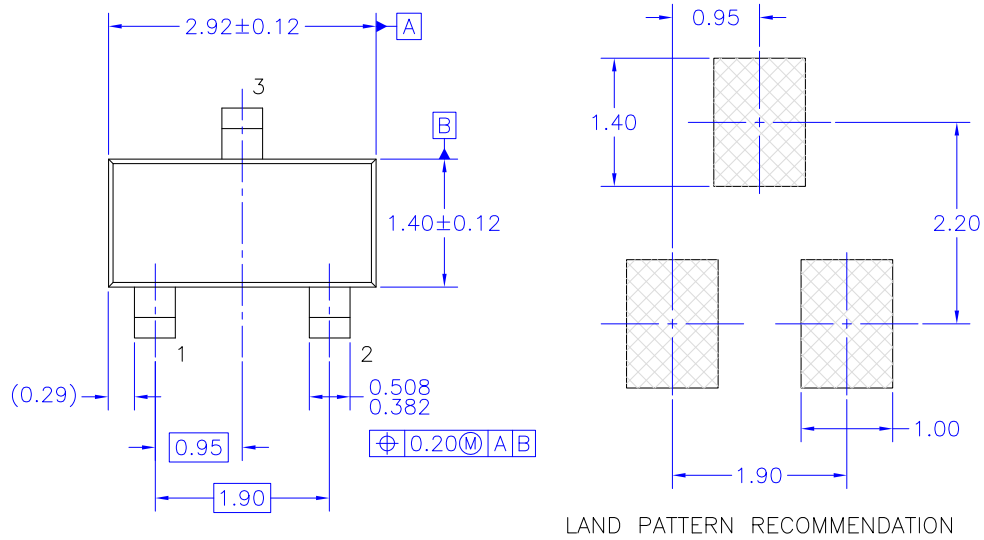


NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREV3.
- E. ON SEMICONDUCTOR

Figure 16. 3-Lead, TO-92, Molded, 0.2 In Line Spacing Lead Form, Ammo, Tape and Reel Type

Physical Dimensions (Continued)



DETAIL A  
SCALE: 50:1

NOTES: UNLESS OTHERWISE SPECIFIED

- A) NO JEDEC REFERENCE AS OF AUGUST 2003
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 1994.

MA03BREV B

Figure 17. MOLDED PACKAGE, SUPERSOT, 3-LEAD

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